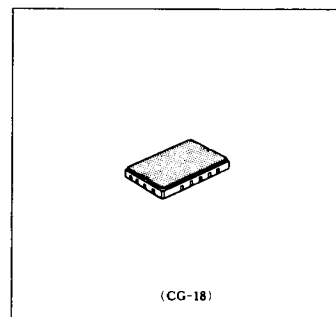


HM4864ACG-12, HM4864ACG-15, HM4864ACG-20

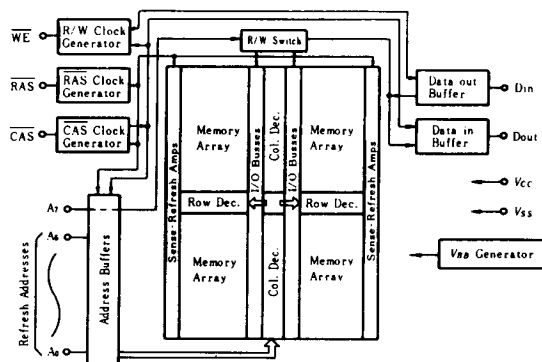
65536-word $\times$ 1-bit Dynamic Random Access Memory

■ FEATURES

- 18-pin Leadless Chip Carrier
- Single 5V ($\pm 10\%$)
- On chip substrate bias generator
- Low Power: 250mW active, 18mW standby
- High speed: Access Time 120/150/200ns (max)
- Common I/O capability using early write operation
- Page mode capability
- Output data controlled by $\overline{\text{CAS}}$
- TTL compatible
- 128 refresh cycles/2ms



■ BLOCK DIAGRAM



■ ABSOLUTE MAXIMUM RATINGS

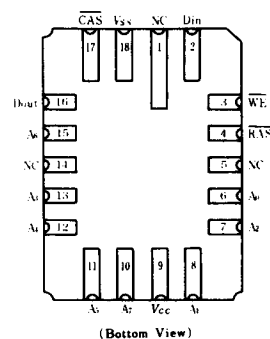
Voltage on any pin relative to V_{SS} -1V to +7V
 Operating temperature, T_a (Ambient) 0°C to $+70^\circ\text{C}$
 Storage temperature -65°C to $+150^\circ\text{C}$
 Power Dissipation 1W
 Short circuit output current 50mA

■ RECOMMENDED DC OPERATING CONDITIONS ($T_a = 0$ to 70°C)

Parameter	Symbol	min.	typ.	max.	Unit	Notes
Supply Voltage	V_{CC}	4.5	5.0	5.5	V	1
Input High Voltage	V_{IH}	2.4	—	6.5	V	1
Input Low Voltage	V_{IL}	-1.0	—	0.8	V	1

Notes : 1. All voltages referenced to V_{SS} .

■ PIN ARRANGEMENT



A0-A7 : Address Inputs
 CAS : Column Address Strobe
 Din : Data In
 Dout : Data Output
 RAS : Row Address Strobe
 WE : Read/Write Input
 VCC : Power (+5V)
 VSS : Ground
 A0-A6 : Refresh Address Inputs

DC ELECTRICAL CHARACTERISTICS ($T_a=0$ to 70°C , $V_{CC}=5\text{V}\pm 10\%$, $V_{SS}=0\text{V}$)

Parameter	Symbol	HM4864ACG-12		HM4864ACG-15		HM4864ACG-20		Unit	Notes
		min	max	min	max	min	max		
Operating Current(RAS,CAS Cycling; $t_{RC}=\text{min}$)	I_{CC1}	—	55	—	50	—	44	mA	1, 2
Standby Current(RAS = V_{IH} , Dout = High Impedance)	I_{CC2}	—	3.5	—	3.5	—	3.5	mA	
Refresh Current(RAS Cycling, CAS = V_{IH} , $t_{RC}=\text{min}$)	I_{CC3}	—	42	—	38	—	33	mA	2
Standby Current(RAS = V_{IH} , Dout Enable)	I_{CC5}	—	5.5	—	5.5	—	5.5	mA	1
Page Mode Current(RAS = V_{IL} , CAS Cycling; $t_{PC}=\text{min}$)	I_{CC4}	—	38	—	35	—	31	mA	1, 2
Input Leakage($0 < V_{in} < 6.5\text{V}$)	I_{LI}	-10	10	-10	10	-10	10	μA	
Output Leakage(Dout is disabled, $0 < V_{out} < 5.5\text{V}$)	I_{LO}	-10	10	-10	10	-10	10	μA	
Output Levels High($I_{out}=-5\text{mA}$)	V_{OH}	2.4	V_{CC}	2.4	V_{CC}	2.4	V_{CC}	V	
Output Levels Low($I_{out}=4.2\text{mA}$)	V_{OL}	0	0.4	0	0.4	0	0.4	V	

Notes) 1. I_{CC} depends on output loading condition when the device is selected, $I_{O\text{ max}}$ is specified at the output open condition.

2. Current depends on cycle rate: maximum current is measured at the fastest cycle rate.

CAPACITANCE ($V_{CC}=5\text{V}\pm 10\%$, $T_a=25^\circ\text{C}$)

Item	Symbol	typ	max	Unit	Notes
Input Capacitance	$A_0 \sim A_7, \text{ Din}$	C_{in1}	—	5	pF
	RAS, CAS, WE	C_{in2}	—	10	pF
Output Capacitance	Dout	C_{out}	—	7	pF

Notes) 1. Capacitance measured with Boonton Meter or effective capacitance measuring method.

2. CAS = V_{IH} to disable Dout.

ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS

($T_a=0$ to 70°C , $V_{CC}=5\text{V}\pm 10\%$, $V_{SS}=0\text{V}$)

Parameter	Symbol	HM4864ACG-12		HM4864ACG-15		HM4864ACG-20		Unit	Notes
		min	max	min	max	min	max		
Access Time From RAS	t_{RAC}	—	120	—	150	—	200	ns	2, 3
Access Time From CAS	t_{CAC}	—	60	—	75	—	100	ns	3, 4
Output Buffer Turn-off Delay	t_{OFF}	—	35	—	40	—	50	ns	5
Transition Time (Rise and Fall)	t_T	3	35	3	35	3	50	ns	6
Random Read or Write Cycle Time	t_{RC}	220	—	260	—	330	—	ns	
RAS Precharge Time	t_{RP}	90	—	100	—	120	—	ns	
RAS Pulse Width	t_{RAS}	120	10000	150	10000	200	10000	ns	
CAS Pulse Width	t_{CAS}	60	10000	75	10000	100	10000	ns	
RAS to CAS Delay Time	t_{RCD}	25	60	25	75	30	100	ns	7
RAS Hold Time	t_{RSH}	60	—	75	—	100	—	ns	
CAS Hold Time	t_{CSH}	120	—	150	—	200	—	ns	
CAS to RAS Precharge Time	t_{CRP}	-10	—	-10	—	-10	—	ns	
Row Address Set-up Time	t_{ASR}	0	—	0	—	0	—	ns	
Row Address Hold Time	t_{RAH}	15	—	15	—	20	—	ns	
Column Address Set-up Time	t_{ASC}	0	—	0	—	0	—	ns	
Column Address Hold Time	t_{CAH}	20	—	25	—	30	—	ns	
Column Address Hold Time Referenced to RAS	t_{AR}	80	—	100	—	130	—	ns	
WE Command Set-up Time	t_{WCS}	0	—	0	—	0	—	ns	8
Write Command Hold Time	t_{WCH}	40	—	45	—	55	—	ns	
Write Command Hold Time Referenced to RAS	t_{WCR}	100	—	120	—	155	—	ns	
Write Command Pulse Width	t_{WP}	40	—	45	—	55	—	ns	
Write Command to RAS Lead Time	t_{RWL}	40	—	45	—	55	—	ns	
Write Command to CAS Lead Time	t_{CWL}	40	—	45	—	55	—	ns	
Data-in Set-up Time	t_{DS}	0	—	0	—	0	—	ns	9
Data-in Hold Time	t_{DH}	40	—	45	—	55	—	ns	9
Data-in Hold Time Referenced to RAS	t_{DHR}	100	—	120	—	155	—	ns	
Read Command Set-up Time	t_{RCS}	0	—	0	—	0	—	ns	
Read Command Hold Time Referenced to CAS	t_{RCH}	0	—	0	—	0	—	ns	
Read Command Hold Time Referenced to RAS	t_{RRH}	10	—	10	—	10	—	ns	
Refresh Period	t_{REF}	—	2	—	2	—	2	ms	
Read-Write Cycle Time	$t_{RW C}$	245	—	280	—	345	—	ns	
CAS to WE Delay	t_{CWD}	40	—	45	—	55	—	ns	8
RAS to WE Delay	t_{RWD}	100	—	120	—	155	—	ns	
Page Mode Cycle Time	t_{PC}	120	—	145	—	190	—	ns	
CAS Precharge Time (for Page-mode Cycle Only)	t_{CP}	50	—	60	—	80	—	ns	
CAS Precharge Time	t_{CPN}	30	—	35	—	45	—	ns	
RAS Precharge to CAS Hold Time	t_{RPC}	0	—	0	—	0	—	ns	

●PAGE MODE WRITE CYCLE

